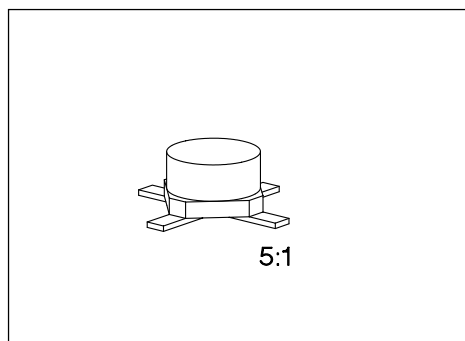


PNP Silicon RF Transistor

BFQ 75

- For broadband amplifiers up to 2 GHz at collector currents from 5 mA to 30 mA.
- Complementary type: BFQ 72 (NPN).



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code (tape and reel)	Pin Configuration				Package ¹⁾
			1	2	3	4	
BFQ 75	75	Q62702-F803	B	E	C	E	Cerec-X

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE0}	12	V
Collector-emitter voltage, $V_{BE} = 0$	V_{CES}	1	
Collector-base voltage	V_{CB0}	15	
Emitter-base voltage	V_{EB0}	2	
Collector current	I_C	50	mA
Total power dissipation, $T_s \leq 112 \text{ }^\circ\text{C}^3$	P_{tot}	350	mW
Junction temperature	T_j	175	$^\circ\text{C}$
Ambient temperature range	T_A	- 65 ... + 175	
Storage temperature range	T_{stg}	- 65 ... + 175	

Thermal Resistance

Junction - ambient ²⁾	$R_{th JA}$	≤ 260	K/W
Junction - soldering point ³⁾	$R_{th JS}$	≤ 180	

1) For detailed dimensions see chapter Package Outlines.

2) Package mounted on alumina 15 mm × 16.7 mm × 0.7 mm.

3) T_s is measured on the collector lead at the soldering point to the pcb.

Electrical Characteristics

at $T_A = 25\text{ °C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

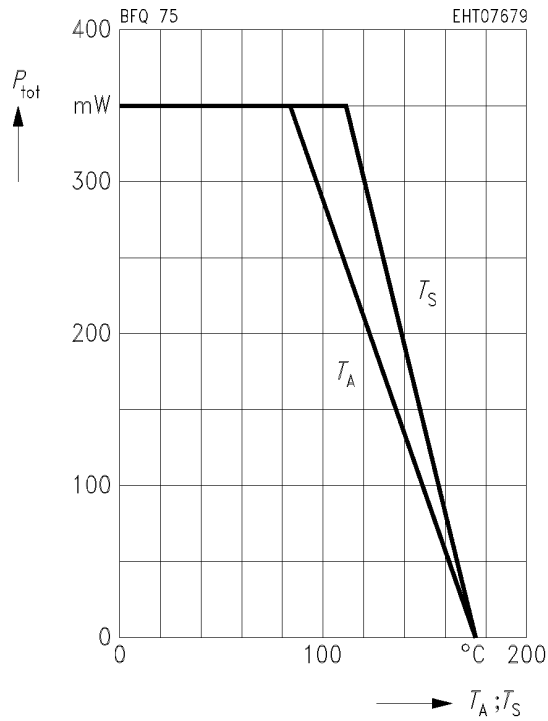
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CE0}$	12	–	–	V
Collector-base cutoff current $V_{CB} = 5\text{ V}, I_E = 0$	I_{CB0}	–	–	50	nA
Emitter-base cutoff current $V_{EB} = 2\text{ V}, I_C = 0$	I_{EB0}	–	–	10	μA
DC current gain $I_C = 30\text{ mA}, V_{CE} = 5\text{ V}$	h_{FE}	20	50	–	–

AC Characteristics

Transition frequency $I_C = 30\text{ mA}, V_{CE} = 5\text{ V}, f = 500\text{ MHz}$	f_T	–	5	–	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}, V_{BE} = v_{be} = 0, f = 1\text{ MHz}$	C_{cb}	–	0.75	–	pF
Input capacitance $V_{EB} = 0.5\text{ V}, I_C = i_c = 0, f = 1\text{ MHz}$	C_{ibo}	–	1.6	–	
Output capacitance $V_{CE} = 10\text{ V}, V_{BE} = v_{be} = 0, f = 1\text{ MHz}$	C_{obs}	–	1.1	–	
Noise figure $I_C = 10\text{ mA}, V_{CE} = 8\text{ V}, f = 10\text{ MHz}, Z_S = 50\ \Omega$ $I_C = 10\text{ mA}, V_{CE} = 8\text{ V}, f = 800\text{ MHz}, Z_S = 50\ \Omega$	F	–	2.2 3	–	dB
Power gain $I_C = 30\text{ mA}, V_{CE} = 8\text{ V}, f = 800\text{ MHz},$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$	G_{pe}	–	14	–	

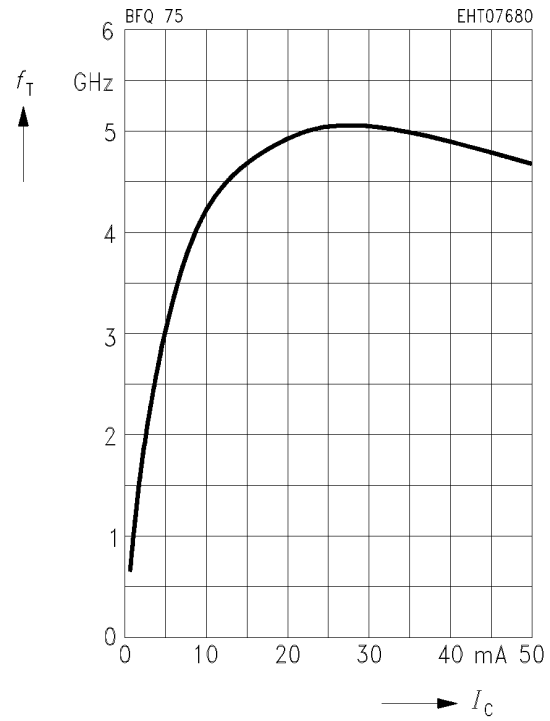
Total power dissipation $P_{tot} = f(T_A^*; T_S)$

*Package mounted on alumina



Transition frequency $f_T = f(I_C)$

$V_{CE} = 5 \text{ V}, f = 500 \text{ MHz}$



Collector-base capacitance $C_{cb} = f(V_{CB})$

$V_{BE} = v_{be} = 0, f = 1 \text{ MHz}$

